

**Notice of References Cited**Application No.  
**09/116,138**Applicant(s)  
**Anthony et al.**Examiner  
**Bernard Souw**Group Art Unit  
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| B | 5,098,623    | 03/24/92 | Pompe          | 264   | 65       |
| C | 4,432,035    | 02/14/84 | Hsieh et al.   | 361   | 322      |
| D | 5,923,056    | 07/13/99 | Lee et al.     | 257   | 192      |
| E | 5,773,325    | 06/30/98 | Teramoto       | 438   | 151      |
| F | 5,874,766    | 02/23/99 | Hori           | 257   | 411      |
| G | 5,504,041    | 04/02/96 | Summerfelt     | 438   | 396      |
| H | 5,876,788    | 03/02/99 | Bronner et al. | 427   | 81       |
| I | 5,851,896    | 12/22/98 | Summerfelt     | 438   | 396      |
| J | 5,187,636    | 02/16/93 | Nakao          | 361   | 313      |
| K | 5,173,835    | 12/22/92 | Cornett et al. | 257   | 310      |
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| M | 5,528,068    | 06/18/96 | Ohmi           | 257   | 410      |

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| V | Shimada et al., "Current drive enhancement by using high-permittivity gate insulator in SOI MOSFET's and its limitation", IEEE Trans. El. Devices, 43/3, 1996, pp. 431-435  | 3/96    |
| W | Shimada et al., "Minimum parasitic resistance for ultra-thin SOI MOSFET with high-permittivity gate insulator performed by lateral contact structure", Proc. 1995 IEEE International SOI Conference, pp. 98-99                    | 10/5/95 |
| X | Chatterjee et al., "CMOS metal replacement gate transistors using tantalum pentoxide gate insulator", IEEE Electron Device Meeting, IEDM '98 Technical Digest, pp. 777-780  | 12/9/98 |

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|  | B | 5,880,006    | 03/09/99 | Lin et al.        | 438    | 424      |
|  | C | 5,851,921    | 12/22/98 | Gardner et al.    | 438    | 655      |
|  | D | 4,227,944    | 10/14/80 | Brown et al.      | 148    | 6        |
|  | E | 4,952,992    | 08/28/90 | Blanchard         | 357    | 23.4     |
|  | F | 5,053,917    | 10/01/91 | Miyasaka et al.   | 361    | 321      |
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|  | K | 3,875,476    | 04/01/75 | Crandall et al.   | F23q 7 | 10       |
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